Title (en)

PRODUCTION OF VDMOS-TRANSISTORS HAVING OPTIMISED GATE CONTACT

Title (de)

HERSTELLUNG VON VDMOS-TRANSISTOREN MIT OPTIMIERTER GATEKONTAKTIERUNG

Title (fr)

PRODUCTION DE TRANSISTORS VDMOS A ETABLISSEMENT DE CONTACT DE GRILLE OPTIMISE

Publication

EP 1869711 A2 20071226 (DE)

Application

EP 06725692 A 20060410

Priority

- EP 2006061497 W 20060410
- DE 102005008191 A 20050413

Abstract (en)

[origin: WO2006108827A2] The invention relates to a method for producing VDMOS-Transistors in which a layer arrangement and the method sequence make it possible to set up an improved gate contact simultaneously with the production of source and gate contacts by means of a single punctured mask (photo mask).

IPC 8 full level

H01L 29/78 (2006.01); **H01L 21/336** (2006.01)

CPC (source: EP US)

H01L 29/66727 (2013.01 - EP US); **H01L 29/7811** (2013.01 - EP US)

Citation (search report)

See references of WO 2006108827A2

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HU IE IS IT LI LT LU LV MC NL PL PT RO SE SI SK TR

DOCDB simple family (publication)

WO 2006108827 A2 20061019; **WO 2006108827 A3 20070201**; DE 102005008191 A1 20061026; DE 102005008191 B4 20101209; EP 1869711 A2 20071226; US 2010035366 A1 20100211; US 8268688 B2 20120918

DOCDB simple family (application)

EP 2006061497 W 20060410; DE 102005008191 A 20050413; EP 06725692 A 20060410; US 91162406 A 20060410